



FINAL PRODUCT/PROCESS CHANGE NOTIFICATIONGeneric Copy

17-Sept-2008**SUBJECT: ON Semiconductor Final Product/Process Change Notification #16150****TITLE: Additional Wafer Fab Capacity for TMOS7 Product****PROPOSED FIRST SHIP DATE: 01-Jan-2009****AFFECTED CHANGE CATEGORY(S): ON Semi FAB Site****AFFECTED PRODUCT DIVISION(S): PowerFET Business Unit****FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:**Contact your local ON Semiconductor Sales Office or Rod Nelson <rod.nelson@onsemi.com>**SAMPLES:** Contact your local ON Semiconductor Sales Office or George Riehm <George.Riehm@onsemi.com>**ADDITIONAL RELIABILITY DATA:** AvailableContact your local ON Semiconductor Sales Office or Donna Scheuch <d.scheuch@onsemi.com>**NOTIFICATION TYPE:**

Final Product/Process Change Notification (FPCN)

Final change notification sent to customers. FPCNs are issued at least 90 days prior to implementation of the change.

ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact your local ON Semiconductor Sales Office.

DESCRIPTION AND PURPOSE:

This is an extension to PCN numbers 12755, 12781, and 12910.

This is an announcement that for the listed products both ON Semiconductor's Wafer Fab facility in Aizu, Japan, and the current Wafer Foundry will be sources for Die. This TMOS7 Silicon platform was originally introduced in 2002 from the Wafer Fab in Aizu. The Aizu Fab facility is fully certified, and has been a continuous source for MOSFET Die for over 20-years.

Device quality and reliability will continue to meet our high standards. The listed products may begin to ship using Die fabricated from the ON Semi-Aizu Wafer Fab facility at the expiration of this PCN.

**Final Product/Process Change Notification #16150****RELIABILITY DATA SUMMARY:**Reliability Test Results, NTD20P06LG Product with Aizu Die:

Test: High Temperature Reverse Bias (HTRB)
Conditions: Vds= 80% Vds rating, Ta=175°C, 1008-Hrs
Results: 0/231

Test: High Temperature Gate Bias (HTGB)
Conditions: Vgs= 100% Vgs rating, Ta=175°C, 1008-Hrs.
Results: 0/231

Test: High Temperature Reverse Bias (HTRB)
Conditions: Vds= 80% Vds rating, Ta=85°C, 1008-Hrs
Results: 0/231

Test: Intermittent Operating Life (IOL-PC)
Conditions: Ta=+25°C, delta Tj=100°C, 2-min on/off, 15K-cycles
Results: 0/231

Test: Temperature Cycling (TC-PC)
Conditions: Ta=-65°C/+150°C, Air-to-Air, Dwell >=10-min, 1000-cy
Results: 0/231

Test: Autoclave Test (AC-PC)
Conditions: Ta=121°C, RH=100%, P=15psig, 96-Hrs
Results: 0/231

Reliability Test Results, NTD20N06G Product with Aizu Die:

Test: High Temperature Reverse Bias (HTRB)
Conditions: Vds= 80% Vds rating, Ta=175°C, 1008-Hrs
Results: 0/231

Test: High Temperature Gate Bias (HTGB)
Conditions: Vgs= 100% Vgs rating, Ta=175°C, 1008-Hrs.
Results: 0/231

Test: High Temperature Reverse Bias (HTRB)
Conditions: Vds= 80% Vds rating, Ta=85°C, 1008-Hrs
Results: 0/231

Test: Intermittent Operating Life (IOL-PC)
Conditions: Ta=+25°C, delta Tj=100°C, 2-min on/off, 15K-cycles
Results: 0/231

Test: Temperature Cycling (TC-PC)
Conditions: Ta=-65°C/+150°C, Air-to-Air, Dwell >=10-min, 1000-cy
Results: 0/231

Test: Autoclave Test (AC-PC)
Conditions: Ta=121°C, RH=100%, P=15psig, 96-Hrs
Results: 0/231

**Final Product/Process Change Notification #16150****ELECTRICAL CHARACTERISTIC SUMMARY:**

There is no change in electrical parametric performance. The Data Sheets will be unchanged. Characterization data is available upon request.

CHANGED PART IDENTIFICATION:

Products having Date Codes of Work Week 01, 2009 and newer may have Die coming from either the ON Semiconductor Wafer facility located in Aizu, Japan, or the subcontractor, Phenitec located in Okayama, Japan.

**Final Product/Process Change Notification #16150****AFFECTED DEVICE LIST**

BS170G
BS170RL1G
BS170RL1
BS170RLRAG
BS170RLRA
BS170RLRMG
BS170RLRM
BS170RLRPG
BS170ZL1G
BS170ZL1
BS170
MMBF170LT1G
MMBF170LT1
MMBF170LT3G
MMBF170LT3
NTR5602NT1
NTR5602NT3
NTP2955G
NTP2955
NTB25P06G
NTB25P06T4G
NTB25P06T4
NTB25P06
NTB5605PG
NTB5605PT4G
NTB5605PT4
NTB5605P
NTB5605T4G
NTD20P06L-001
NTD20P06L-1G
NTD20P06LG
NTD20P06LT4G
NTD20P06LT4
NTD20P06L
NTD2955-001
NTD2955-1G
NTD2955G
NTD2955PT4G
NTD2955T4G
NTD2955T4
NTD2955
NTDV20P06LT4G
NTF2955PT1G
NTF2955T1G
NTF2955T1
STD20P06LT4
STD20P07LT4G
STD2955T4G
STD2955T4
STD3055L104T4
STD3155L104T4
STD6789T4
SMBF1026LT1G
SMBF1026LT1